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[45] Date of Patent:

May 23, 1995

Harari et al.

[54]	FLASH	EEPROM	SYSTEM	WITH	ERASE
	SECTOR	R SELECT			

United States Patent [19]

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Calif.

[21] Appl. No.: 963,851

[22] Filed: Oct. 20, 1992

Related U.S. Application Data

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	doned.								

[51] Int. Cl.6 G11C 7/00

365/900

[58] Field of Search 365/185, 218, 900, 230.03

[56] References Cited

U.S. PATENT DOCUMENTS

OTHER PUBLICATIONS

R. Wilson, "1-Mbit flash memories seek their role in

system design", Computer Design, Mar. 1, 1989, pp. 30 and 32.

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[57] ABSTRACT

A system of Flash EEprom memory chips with controlling circuits serves as non-volatile memory such as that provided by magnetic disk drives. Improvements include selective multiple sector erase, in which any combinations of Flash sectors may be erased together. Selective sectors among the selected combination may also be de-selected during the erase operation. Another improvement is the ability to remap and replace defective cells with substitute cells. The remapping is performed automatically as soon as a defective cell is detected. When the number of defects in a Flash sector becomes large, the whole sector is remapped. Yet another improvement is the use of a write cache to reduce the number of writes to the Flash EEprom memory, thereby minimizing the stress to the device from undergoing too many write/erase cycling.

4 Claims, 5 Drawing Sheets

